NOT RECOMMENDED FOR NEW DESIGN USE BSS138-7-F



BSS138(Z)

50V N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET IN SOT23

Features and Benefits

- BV_{DSS} > 50V
- $R_{DS(on)} \le 3.5\Omega$ @ $V_{GS} = 5V$
- Maximum Continuous Drain Current I_D = 200mA
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

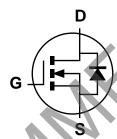
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)

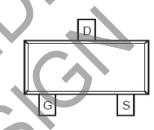
SOT23



Top View



Device symbol



Pin-Out Top View

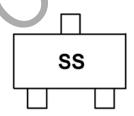
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
BSS138TA	SS	7	8	3000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- <1000ppm antimony compounds.</p>
 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



SS = Product Type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	50	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current	I _D	200	mA
Pulsed Drain Current (Note 6)	I _{DM}	800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

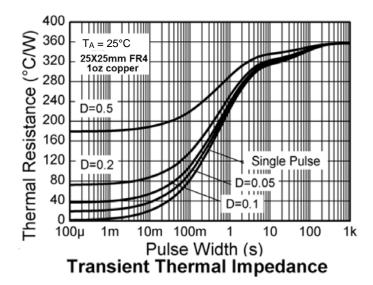
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P _D	350	mW
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\Theta JA}$	357	°C/W
Thermal Resistance, Junction to Leads	(Note 7)	R _{ÐJL}	195	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

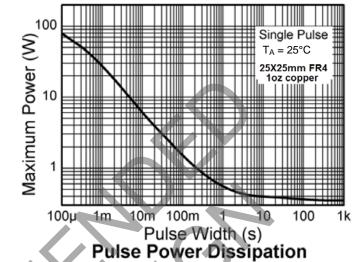
Notes:

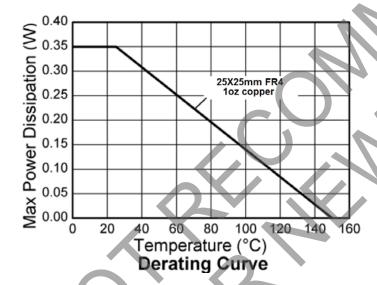
- 5. For a device mounted on 25mm × 25mm × 1.6mm FR-4 PCV with high coverage of single sided 1oz copper, in still air condition.
- 6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).



Thermal Characteristics









Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	50	_		V	$V_{GS} = 0V, I_D = 0.25mA$
				0.5	μΑ	$V_{DS} = 50V$, $V_{GS} = 0V$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	5	μA	$V_{DS} = 50V, V_{GS} = 0V, T_A = +125$ °C
				100	nA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}			±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	_	1.5	V	$V_{DS} = V_{GS}$, $I_D = 1mA$
Static Drain-Source On-Resistance (Note 8)	R _{DS(on)}			3.5	Ω	$V_{GS} = 5V, I_D = 200mA$
Forward Transconductance (Notes 8 & 9)	g fs	120	_	-	mS	$V_{DS} = 25V, I_D = 200mA$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	_	_	50	pF	25)/)/
Output Capacitance	Coss	_	_	25	pF	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0MHz$
Reverse Transfer Capacitance	C _{rss}	_	_	8	pF	1 = 1.0IVII 12
Turn-On Delay Time (Note 10)	t _{D(on)}	_	10	-	ns	
Turn-On Rise Time (Note 10)	t _r	_	10		ns	V 00V/1 000×4
Turn-Off Delay Time (Note 10)	t _{D(off)}	_	15	_	ns	$V_{DD} = 30V$, $I_D = 280mA$
Turn-Off Fall Time (Note 10)	t _f		25		ns	

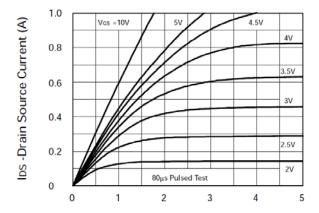
Notes:



^{8.} Measured under pulsed conditions. Width = 300μs. Duty cycle ≤ 2%.
9. Sample test.
10. Switching times measured with 50Ω source impedance and <5ns rise time on a pulse generator.

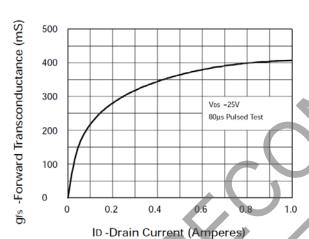


Electrical Characteristics (continued)



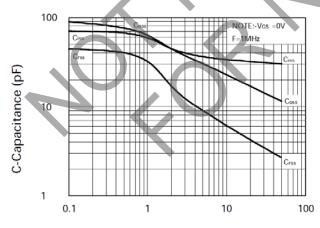
VDS -Drain Source Voltage (Volts)

Saturation Characteristics



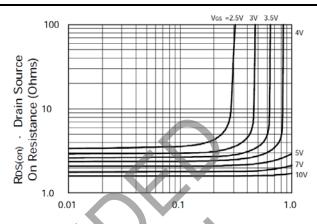
Typical Transconductance vs.

Drain Current



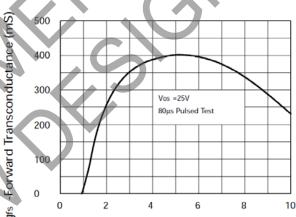
VDS -Drain Source Voltage (Volts)

Typical Capacitance vs. Drain - Source Voltage



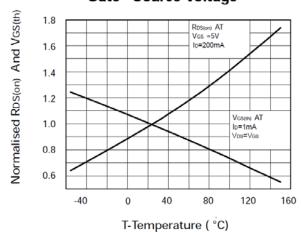
D-Drain Current (Amperes)

Typical On Resistance vs. Drain Current



VGS -Gate Source Voltage (Volts)

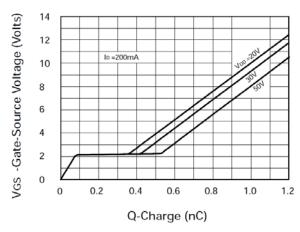
Typical Transconductance vs. Gate - Source Voltage



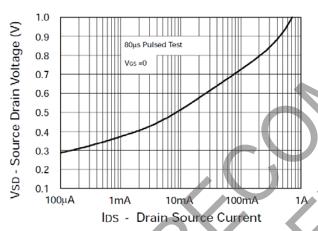
Normalised RDS(on) And VGS(th) vs. Temperature



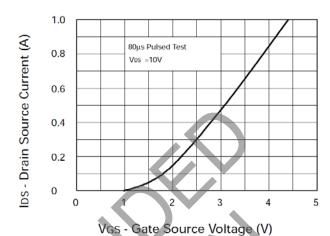
Electrical Characteristics (cont.)



Typical Gate Charge vs. Gate-Source Voltage



Typical Diode Forward Voltage

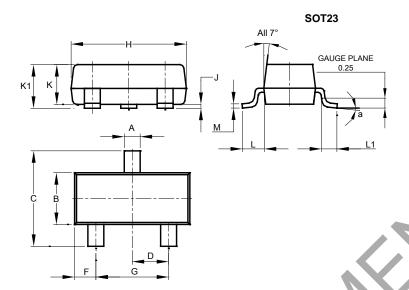


Typical Transfer Characteristics



Package Outline Dimensions

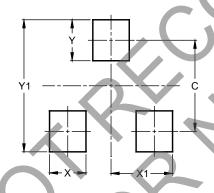
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
H	2.80	3.00	2.90		
7	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
١	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
M	0.085	0.150	0.110		
а	0°	8°			
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)		
С	2.0		
Х	0.8		
X1	1.35		
Y	0.9		
Y1	2.9		

SOT23



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